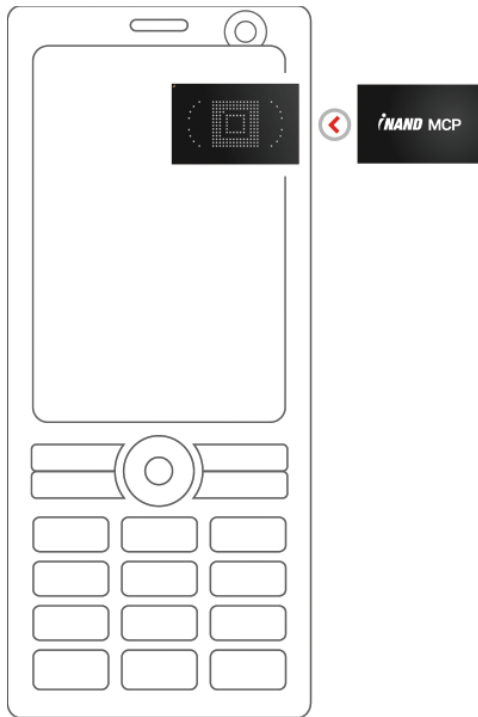With every new generation of mobile multimedia handsets, more applications are converging into a single device. Feature-rich handsets offer music playback, high-quality video and TV applications, navigation services and gaming. More embedded storage lets users enrich their multimedia lifestyle.

The SanDisk® iNAND™-based multichip package (MCP) offers a range of high-capacity storage and low power DRAM combinations. They all share the same standard architecture, footprint and package. A single device enables tailored storage, code execution and boot requirements to free up precious real estate, reduce design complexity and give design-ers the flexibility and scalability to support multiple handset designs.

Main Features and Benefits

Catering to Diverse Memory Needs

The SanDisk iNAND-based MCP offers iNAND eSD/eMMC high-capacity storage of up to 8GB with a high-performance, low-power DRAM up to 2Gb (256MB), packaged in a small, standard form factor.

MLC NAND flash controller

Low Power DRAM

MLC NAND Flash

High-Capacity Data Storage

iNAND eSD/eMMC device uses SanDisk advanced, cost-effective multi-level cell (MLC) NAND flash tech-nology, a flash controller and embedded flash man-agement firmware. Handset designers enjoy ease of integration, reliability and high-performance perfectly suited for mobile multimedia applications.

Code Storage and System Boot

iNAND eSD/eMMC, based on SanDisk MLC NAND flash technology, is a reliable code storage and boot device. It eliminates the need for an additional boot code storage device and a NAND interface, substan-tially reducing system design complexity and cost.

iNAND eSD – The Perfect System Solution

Dedicated physical partitions - managed by customiz-able levels of protection and with a power failure im-munity mechanism - now allow boot code to be safely stored on the iNAND device and and accessed via the eSD interface.
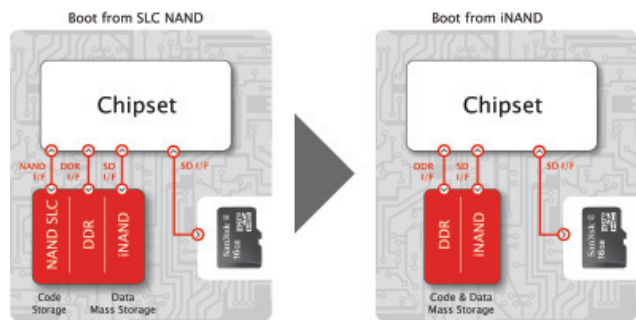
SanDisk®

Low-Power System DRAM

SanDisk iNAND-based MCPs incorporate industry standard, high-performance, low-power DRAM, designed especially for mobile devices. SanDisk technology ensures MCP design is optimized to meet the strict signal integrity and power routing require-ments of high-speed LP-DRAM (DDR), without com-promising package height and cost constraints.

Optimized for Smooth Migration

SanDisk iNAND-based MCP provides a flexible and scalable solution for various memory configuration requirements. It supports seamless migration to fu-ture designs, including boot from iNAND eSD/eMMC via a standard interface.

Because iNAND-based MCP devices of various con-figurations, capacities and package sizes share the same architecture and ballout, one platform design can be used for various handset models.

More Reliable

SanDisk brings a wealth of experience and cutting edge technology to MCP design. SanDisk employs advanced packaging, stacking, assembly and testing technologies to provide highly reliable and efficient packaging.

Why iNAND-Based MCP?

- **Advanced flash technology** – Access the latest generation of SanDisk advanced MLC NAND flash technology.
- **Standard interface and form factor** – Make ntegration a breeze with the eSD and eMMC standard interfaces.
- **High performance** – Provide 15MB/s sustained read and 9MB/s sustained write.

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SanDisk iNAND-Based MCP Family of Products

	iNAND	LP DRAM
Capacity**	4Gb-64Gb (512MB-8GB)	1-2Gb
Interface	eSD/eMMC	DDR 32bit I/F
NAND flash technology	SanDisk MLC	N/A
Flash management	Embedded firmware	N/A
Performance	Sustained read: 15MB/sec Sustained write: 9MB/sec	166MHz
Operating voltage	Core: 1.8V/3.3V I/O: 1.8V/3.3V	1.8V/1.8V
Package (mm)	12x16	
Power-save mode	350µA	
Active current	Default: 100mA High speed: 200mA	Active current: max 75mA

* 1 gigabyte (GB) = 1 billion bytes; 1 megabyte (MB) = 1 million bytes; speed based on internal testing; performance may be lower depending on host device. Some capacity not available for data storage.
** Note these are capacity ranges for reference only. Not all iNAND and DRAM capacities are available.

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